MS20-P7 In-situ reduction of as-prepared γ-Iron Oxide Nanoparticles

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Magnetic materials are a hot topic among energy-materials and they find applications in nearly all everyday consumer electronics. Advances in magnetic performance have in particular been made for thin film and nanosized particles, because the magnetic properties are strongly related to the size. Bulk iron is relatively unreactive, however iron on the form of nanoparticles are highly reactive due to the enlarged surface area and the oxidation potential of iron. Iron oxides are cheap and unreactive precursors for the production of nanosized iron particles. Understanding the mechanisms behind the structural development [1, 2] adds to the fundamental understanding of materials' formation and can lead to new synthesis pathways. In this study, iron oxide (γ-Fe_2O_3) particles were heated to 400°C under a flow of H_2/Ar mixture, while the process was followed by *in situ* synchrotron powder X-ray diffraction measurement. The as-prepared maghemite nanoparticles were synthesized by the continuous decomposition of solutes in supercritical hydrothermal flow synthesis [3, 4]. The reagent used was ferric ammonium citrate ($C_6H_8O_7$•xFe(III)•yNH_3) that under hydrothermal flow synthesis decomposes into the γ-iron oxide Fe_2O_3. The reduction of maghemite to body centered cubic (BCC) iron does not go through a detectable intermediate state.

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Keywords: In situ PXRD, reduction, maghemite, iron oxides, magnetic materials

MS21 Structural disorder and materials' properties at ambient and non-ambient conditions

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MS21-P1 HRXRD analysis of bonded Si / Si interface

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Stress and strain can not only influence the structural behavior of the materials but can significantly alter their functional properties. The need for local, nanoscale characterization of stress levels and its correlation with other material properties increases rapidly. Scanning X-ray microscopy using synchrotron radiation is an emergent technique which can deliver fast, conclusive results with *submicrometer real space* resolution [1,2]. On the other hand the technique is limited in its *reciprocal space* resolution by the pixel size of 2D detectors. This is especially important if high quality single crystals have to be characterized. Modern laboratory instruments therefore offer the complementary capability owing to their higher reciprocal space resolution.

In this study we investigated the stress distribution in Si wafer pairs which were covalently bonded at room temperature [3]. The wafer bonds were analyzed by the "nanodiffraction" ID01 beamline at ESRF (F) [1] as well as by a Bruker D8 Davinci HRXRD instrument at EMPA (CH). Transmission electron microscopy (TEM) was used for morphological analysis. The specific wafer bond shown in Fig. 1 exhibited bulk bond strength, but contained a ~ 3 nm thick amorphous interfacial layer in their as-prepared form. After high temperature annealing a network of dislocations emerged to compensate for rotation and tilt of the two wafers.

The built-in stress at the interface caused some long range changes in the diffraction patterns, which can easily be distinguished by lower spatial resolution laboratory scale devices. The evaluation of the rocking curve FWHM going through the bonding interface cross section (X-ray beam size 50mm) shows the overall silicon crystal

quality summing up in strain and geometrical behavior (Fig.1a). At the interface, dislocations in the annealed specimens (Fig. 1b) caused a broadening of the Si(333) reflection (Fig. 1c).

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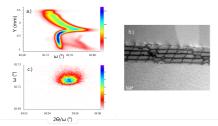[3] C. Flötgen, N. Razek, V. Dragoi and M. Wimplinger, ECS Transactions 64 (2014) 103.

Figure 1. Spatially resolved RCs for an as prepared specimen showing strain/tilt components (a). TEM picture showing dislocation density patterns (b). Reciprocal space map (RSM) on the Si(333) reflection from the annealed Si/Si interface (c), the dislocations caused a more diffuse Bragg-peak.

Keywords: reciprocal space mapping, stress analysis, bonded silicon, dislocations

MS21-P2 Synthesis, structures and luminescence properties of two gallium(III) complexes containing 5,7dimethyl-8-hydroxyquinoline.

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Metal-quinolinates are known as key materials in the design of organic light emitting diode (OLEDs) devices since their discovery by Tang and Van Slyke back in 1987.[1] Quinolinol derivatives have been since envisaged as promising fluorophores. As a result, that has prompted growth in the science of these $M(Ox)_3$ entities with other icosagens down the boron group such as gallium (Ga) and indium (In).[2,3] Not only has there been extensive research on the structural discrepancies of these type of complexes leading to isomerization (*mer/fac*), but also, the net effect (in the solid state) imposed by the guest molecules trapped in the unit cell. Crystallography in particular, provided an excellent technique for the investigation of the net effect in these complexes w.r.t. to inter-molecular interactions therein and the solvento species "trapped" within the crystal lattice.[4]

In this work, two complexes of $M(Ox)_3$ (M = Ga(III), OxH = 5,7 dimethyl-8-hydroxyquinoline) have been synthesized and characterized by ^{1}H NMR, ^{13}C NMR, single crystal X-ray Diffraction and SEM, and their photoluminescence properties evaluated. The fact that crystals were obtained with a different number of dichloromethane molecules in the crystal lattice, provides the rare opportunity to investigate solvent effects in photoluminescence.

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